N-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a		
60	0.0038 at V _{GS} = 10 V	65		
	0.0057 at V _{GS} = 4.5 V	55		

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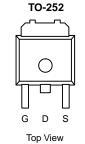
SEMICONDUCTOR

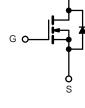
FEATURES

- 175 °C Junction Temperature
- DT-Trench Power MOSFET

D

• Material categorization:





N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 1$	25 °C, unless othe	rwise noted)			
Parameter	Symbol	Limit	Unit		
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 175 °C) ^b	T _C = 25 °C	1	65		
	T _C = 100 °C	I I _D	55 ^a		
Pulsed Drain Current		I _{DM}	195	А	
Continuous Source Current (Diode Conduction)		۱ _S	65 ^a		
Avalanche Current		I _{AS}	60		
Single Avalanche Energy (Duty Cycle \leq 1 %)	L = 0.1 mH	E _{AS}	155	mJ	
Mariana Dissission	T _C = 25 °C	D	159	10/	
Maximum Power Dissipation	T _A = 25 °C	P _D	4 ^b , 8.9 ^{b, c}	W	
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manianum lumation to Arabianta	$t \le 10 \text{ sec}$	P	12	18	°C/W
Maximum Junction-to-Ambient ^a	Steady State	R _{thJA}	35	50	
Maximum Junction-to-Case		R _{thJC}	0.84	1.1	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t \leq 10 s.





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SPECIFICATIONS ($T_J = 25$	°C, unless o	otherwise noted)					
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1	2	3		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA	
	I _{DSS}	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 \text{ °C}$			50		
		$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 175 \text{ °C}$			250		
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	50			А	
		V _{GS} = 10 V, I _D = 10 A		0.0038	0.0045	Ω	
	P	V _{GS} = 10 V, I _D = 10 A, T _J = 125 °C		0.0040	0.0049		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A, T _J = 175 °C		0.0042	0.0051		
		V _{GS} = 4.5 V, I _D = 5 A		0.0057	0.0069		
Forward Transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 10 A		60		S	
Dynamic	•						
Input Capacitance	C _{iss}			10950		pF	
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		3570			
Reverse Transfer Capacitance	C _{rss}			225			
Total Gate Charge ^c	Qg			47	70	nC	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 30 V, V_{GS} = 10 V, I_{D} = 50 A		10			
Gate-Drain Charge ^c	Q _{gd}			12			
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	$V_{DD} = 30 \text{ V}, \text{ R}_{L} = 0.6 \Omega$ $\text{I}_{D} \cong 50 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{g} = 2.5 \Omega$		15	25	ns	
Turn-Off Delay Time ^c	t _{d(off)}			35	50		
Fall Time ^c	t _f			20	30		
Source-Drain Diode Ratings and Ch	aracteristics (T _C = 25 °C)		<u> </u>	· · · · · ·		
Pulsed Current	I _{SM}				195	А	
Diode Forward Voltage	V _{SD}	$I_{F} = 20 \text{ A}, V_{GS} = 0 \text{ V}$		1	1.5	V	
Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/µs		45	100	ns	

Notes:

a. For design aid only; not subject to production testing.

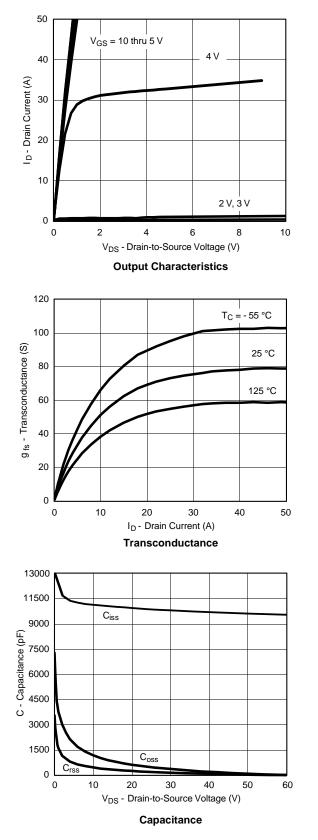
b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

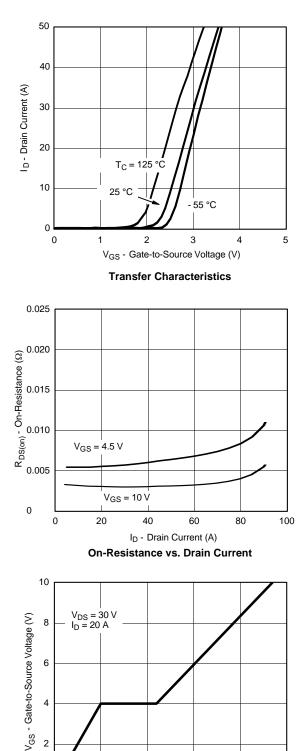
c. Independent of operating temperature.

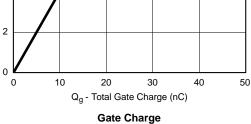
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25 °C unless noted)

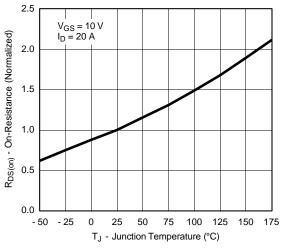




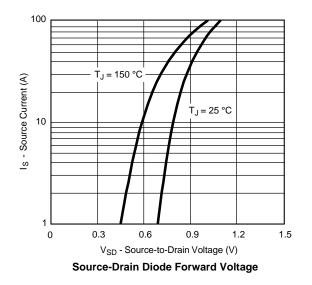




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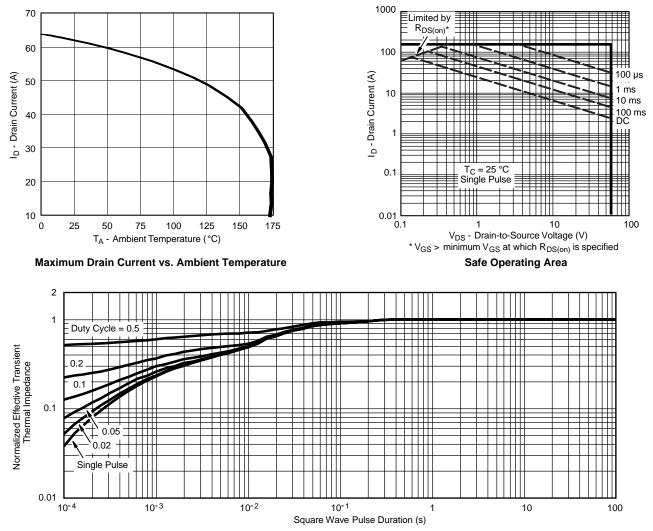


On-Resistance vs. Junction Temperature





THERMAL RATINGS



Normalized Thermal Transient Impedance, Junction-to-Case

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